Expectation to the future developments

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Resistance Change Memories (RCM) including ReRAM, PRAM and atomic switch have recently attracted much attention as next-generation nonvolatile memories with low power consumption and high-speed operation. However, it is urgent to improve the device structures and elucidate the principles of operation for the practical applications and high performances of these memories. Nevertheless, hardly any symposiums focused on RCM have been carried out in Annual Meetings of JSAP. Under these circumstances, this symposium was organized by Silicon Technology Division and Thin Film & Surface Physics Division of JSAP for the purpose of comprehensive discussions on RCM.

Another feature of this symposium is to invite a few overseas researchers from Taiwan and Korea with many domestic influential researchers by considering high activities in East Asian countries. It is strongly expected that the present status of RCM will be clarified and the directivity of future development will be found out by the active discussions.